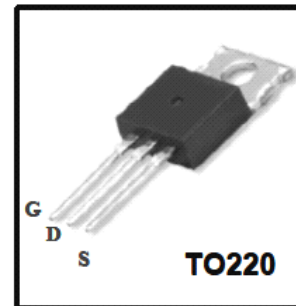
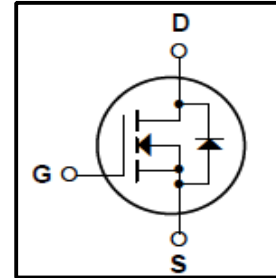


**Silicon N-Channel MOSFET**
**Features**

- 8A,500V,RDS(on)(Max 0.8Ω)@VGS=10V
- Ultra-low Gate Charge(Typical 59nC)
- Fast Switching Capability
- 100%Avalanche Tested
- Maximum Junction Temperature Range(150°C)


**General Description**

This Power MOSFET is produced using Winsemi's advanced planar stripe, DMOS technology. This latest technology has been especially designed to minimize on-state resistance, have a high rugged avalanche characteristics. This devices is specially well suited for high efficiency switch model power supplies, power factor correction and half bridge and full bridge resonant topology line a Electronic lamp ballast.

**Absolute Maximum Ratings**

Symbol	Parameter	Value	Units
V <sub>DSS</sub>	Drain Source Voltage	500	V
I <sub>D</sub>	Continuous Drain Current(@Tc=25°C)	8	A
	Continuous Drain Current(@Tc=100°C)	5.1	A
I <sub>DM</sub>	Drain Current Pulsed (Note1)	32	A
V <sub>GS</sub>	Gate to Source Voltage	±30	V
E <sub>AS</sub>	Single Pulsed Avalanche Energy (Note 2)	320	mJ
E <sub>AR</sub>	Repetitive Avalanche Energy (Note 1)	13.4	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	3.5	V/ns
P <sub>D</sub>	Total Power Dissipation(@Tc=25°C)	134	W
	Derating Factor above 25°C	1.0	W/°C
T <sub>J</sub> , T <sub>stg</sub>	Junction and Storage Temperature	-55~150	°C
T <sub>L</sub>	Channel Temperature	300	°C

\*Drain current limited by junction temperature

**Thermal Characteristics**

Symbol	Parameter	Value			Units
		Min	Typ	Max	
R <sub>QJC</sub>	Thermal Resistance, Junction-to-Case	-	-	0.93	°C/W
R <sub>QCS</sub>	Thermal Resistance, Case-to-Sink	-	0.5	-	°C/W
R <sub>QJA</sub>	Thermal Resistance, Junction-to-Ambient	-	-	62	°C/W

**Electrical Characteristics (T<sub>c</sub> = 25<sup>o</sup> C)**

Characteristics	Symbol	Test Condition	Min	Type	Max	Unit	
Gate leakage current	I <sub>GSS</sub>	V <sub>GS</sub> = ±30 V, V <sub>DS</sub> = 0 V	-	-	±100	nA	
Gate-source breakdown voltage	V <sub>(BR)GSS</sub>	I <sub>G</sub> = ±10 μA, V <sub>DS</sub> = 0 V	±30	-	-	V	
Drain cut-off current	I <sub>DSS</sub>	V <sub>DS</sub> = 400 V, V <sub>GS</sub> = 0 V	-	-	10	μA	
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> = 250 μA, V <sub>GS</sub> = 0 V	500	-	-	V	
Break Voltage Temperature Coefficient	ΔBV <sub>DSS</sub> /ΔT <sub>J</sub>	I <sub>D</sub> =250μA, Referenced to 25°C	-	0.5	-	V/°C	
Gate threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> =250 μA	2	-	4	V	
Drain-source ON resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 4.0A	-	-	0.80	Ω	
Forward Transconductance	g <sub>fs</sub>	V <sub>DS</sub> = 40 V, I <sub>D</sub> = 4.0A	-	7.3	-	S	
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 25 V,	-	1400	1800	pF	
Reverse transfer capacitance	C <sub>rss</sub>	V <sub>GS</sub> = 0 V,	-	34	44		
Output capacitance	C <sub>oss</sub>	f = 1 MHz	-	145	190		
Switching time	Rise time	t <sub>r</sub>	V <sub>DD</sub> =250 V, I <sub>D</sub> =8A R <sub>G</sub> =9.1Ω R <sub>D</sub> =31Ω (Note4,5)	-	22	55	ns
	Turn-on time	t <sub>on</sub>		-	65	140	
	Fall time	t <sub>f</sub>		-	125	260	
	Turn-off time	t <sub>off</sub>		-	75	160	
Total gate charge (gate-source plus gate-drain)	Q <sub>g</sub>	V <sub>DD</sub> = 400 V, V <sub>GS</sub> = 10 V, I <sub>D</sub> = 8 A (Note4,5)	-	59	70	nC	
Gate-source charge	Q <sub>gs</sub>		-	7	9		
Gate-drain ("miller") Charge	Q <sub>gd</sub>		-	28	32		

**Source-Drain Ratings and Characteristics (T<sub>a</sub> = 25<sup>o</sup> C)**

Characteristics	Symbol	Test Condition	Min	Type	Max	Unit
Continuous drain reverse current	I <sub>DR</sub>	-	-	-	8	A
Pulse drain reverse current	I <sub>DRP</sub>	-	-	-	32	A
Forward voltage (diode)	V <sub>DSF</sub>	I <sub>DR</sub> = 8 A, V <sub>GS</sub> = 0 V	-	-	1.4	V
Reverse recovery time	t <sub>rr</sub>	I <sub>DR</sub> = 8 A, V <sub>GS</sub> = 0 V, dI <sub>DR</sub> / dt = 100 A / μs	-	390	-	ns
Reverse recovery charge	Q <sub>rr</sub>		-	4.2	-	μC

Note 1.Repeativity rating :pulse width limited by junction temperature

2.L=9mH,I<sub>AS</sub>=8A,V<sub>DD</sub>=50V,R<sub>G</sub>=25Ω,Starting T<sub>J</sub>=25°C

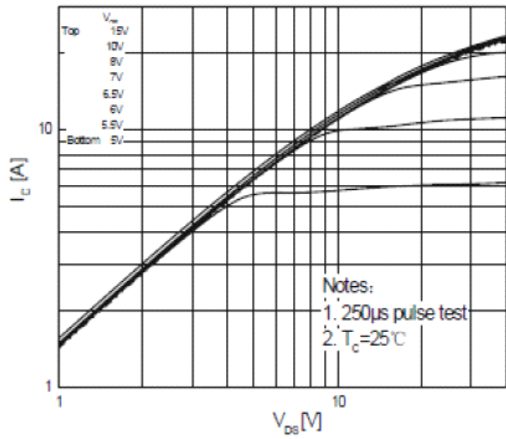
3.I<sub>SD</sub>≤8A,di/dt≤300A/us, V<sub>DD</sub><BV<sub>DSS</sub>,STARTING T<sub>J</sub>=25°C

4.Pulse Test: Pulse Width≤300us,Duty Cycle≤2%

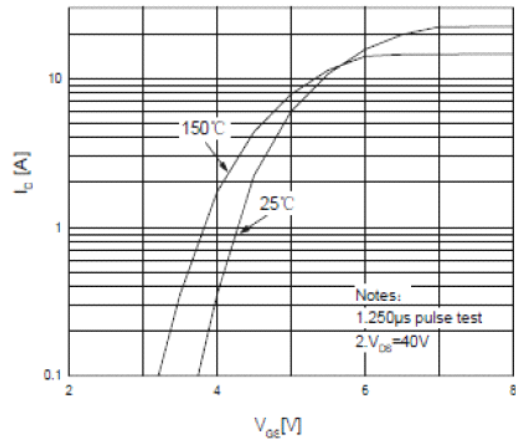
5.Essentially independent of operating temperature.

This transistor is an electrostatic sensitive device

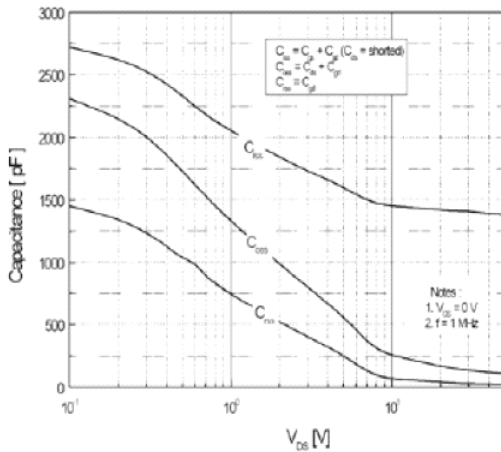
Please handle with caution



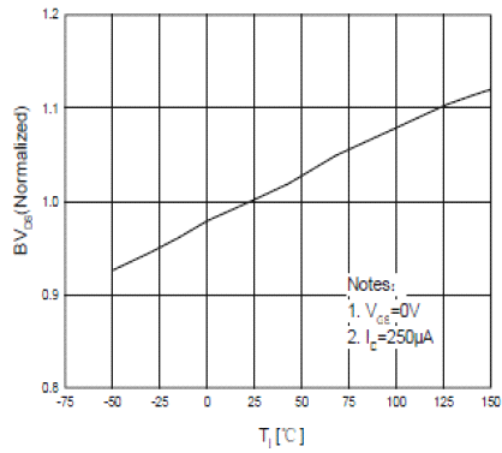
**Fig. 1 On-State Characteristics**



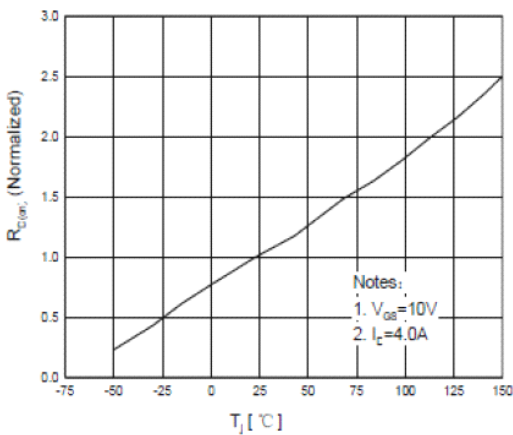
**Fig.2 Transfer Characteristics**



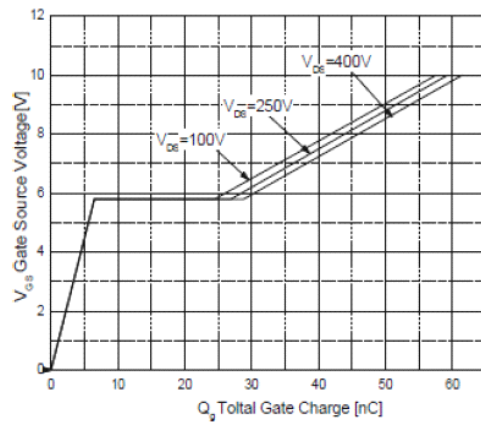
**Fig.3 Capacitance Variation vs Drain Voltage**



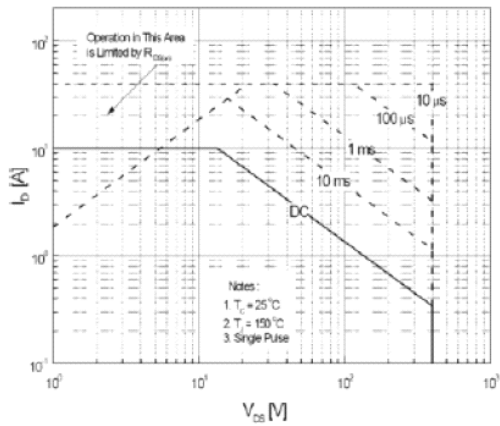
**Fig.4 Maximum Avalanche Energy vs On-State Current**



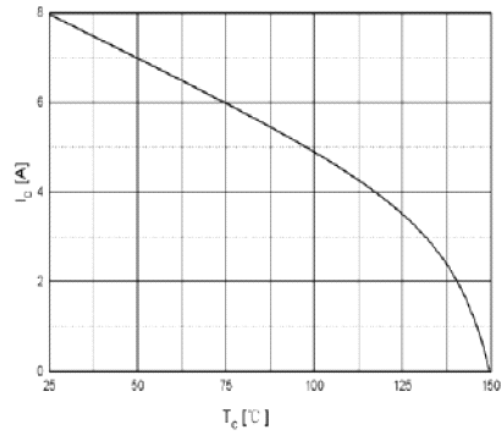
**Fig.5 On-Resistance Variation vs Junction Temperature**



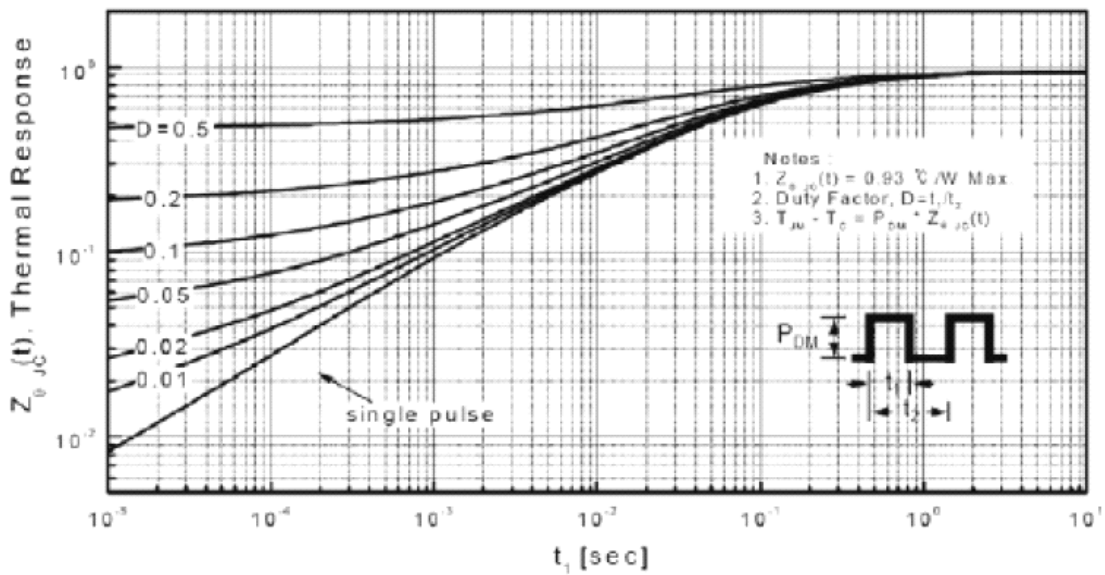
**Fig.6 Gate Charge Characteristics**



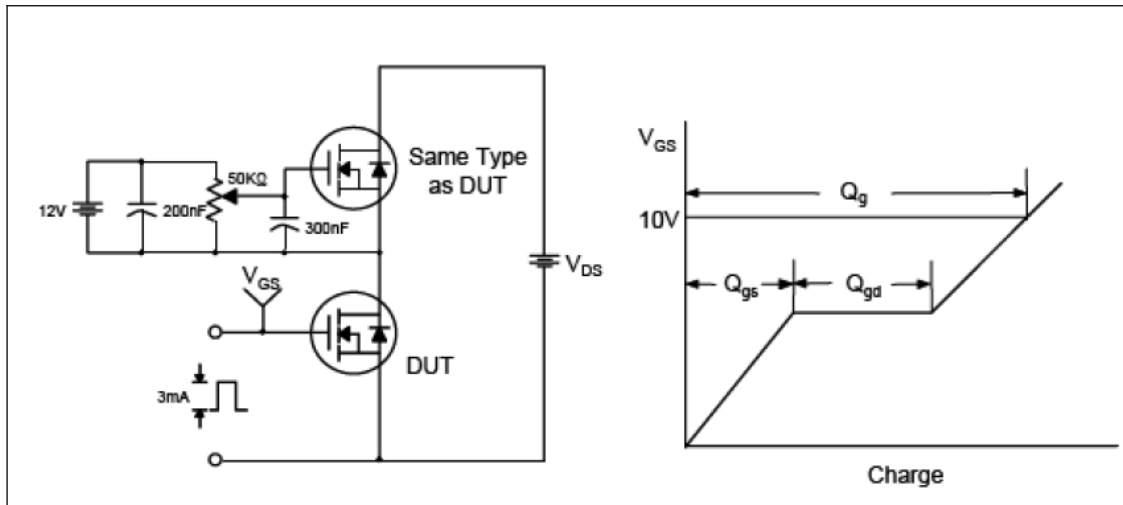
**Fig.7 Maximum Safe Operation Area**



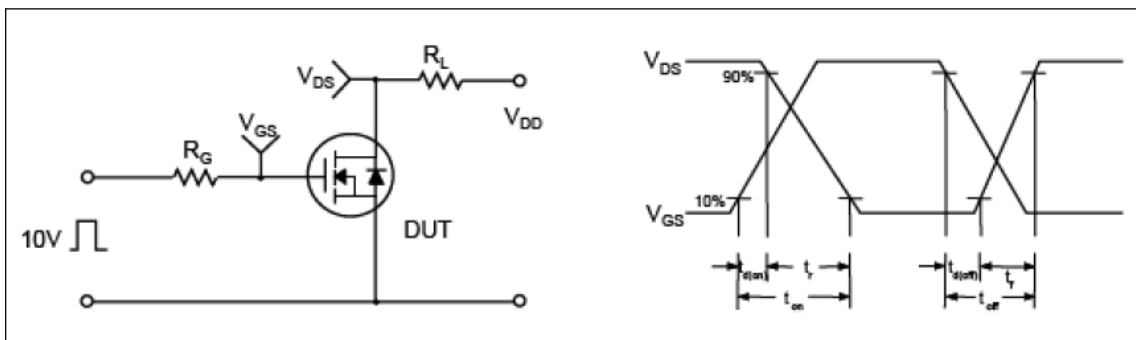
**Fig.8 Maximum Drain Current vs Case Temperature**



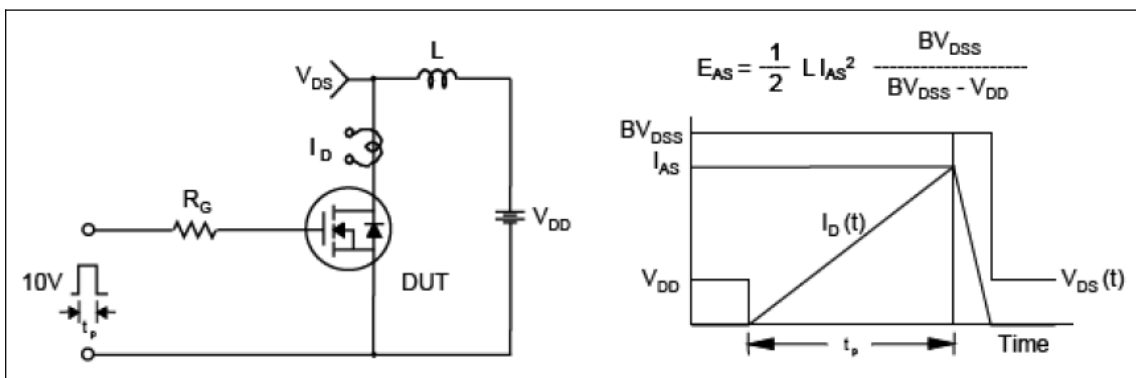
**Fig.9 Transient Thermal Response Curve**



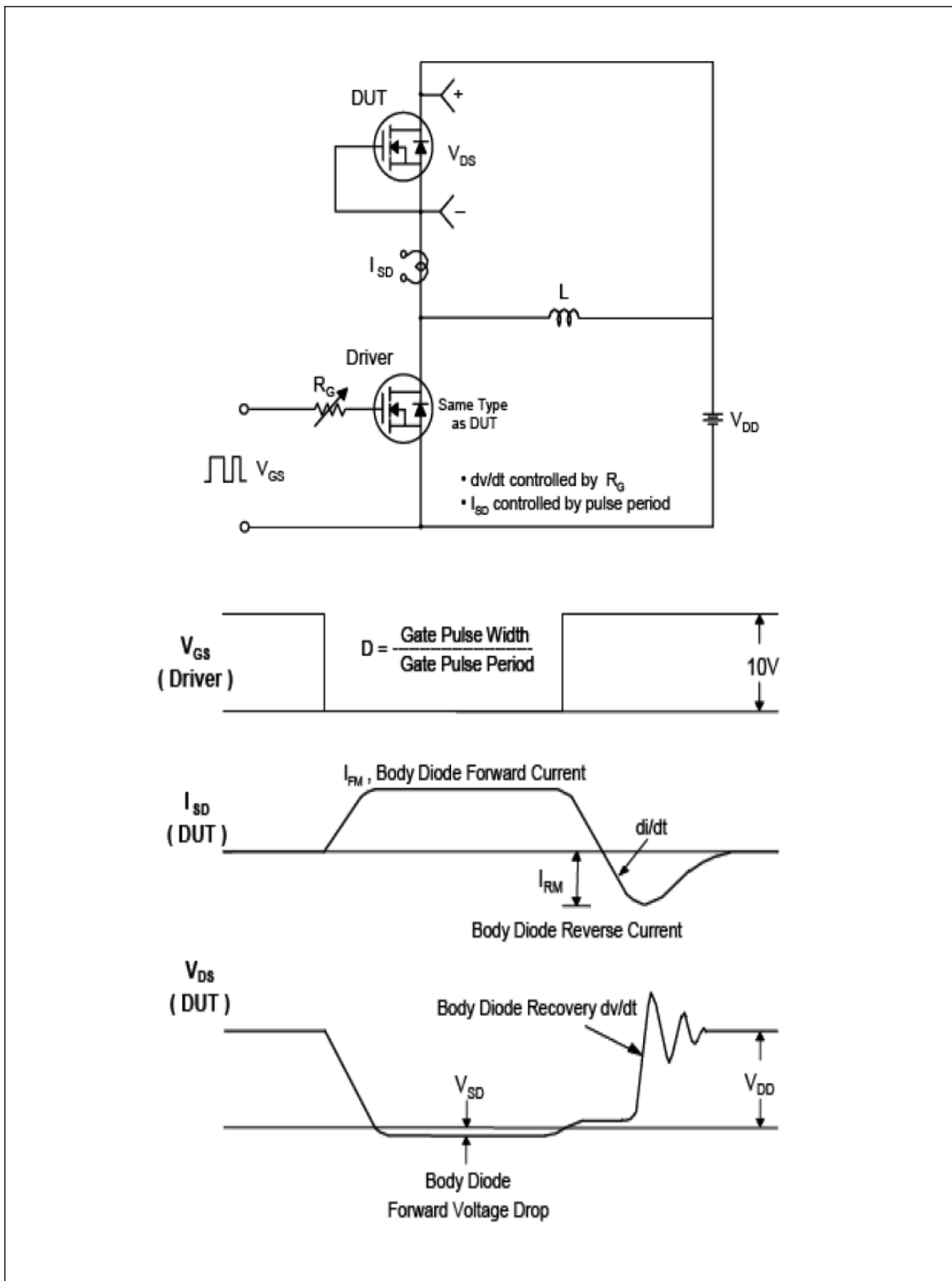
**Fig.10 Gate Test Circuit & Waveform**



**Fig.11 Resistive Switching Test Circuit & Waveform**



**Fig.12 Unclamped Inductive Switching Test Circuit & Waveform**



**Fig.13 Peak Diode Recovery  $dv/dt$  Test Circuit & Waveform**

**TO-220C Package Dimension**

